



### CST15N10Z N-Ch 100V Fast Switching MOSFETs

- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent Cdv/dt effect decline
- ★ Advanced high cell density Trench technology

#### CST15N10Z Product Summary



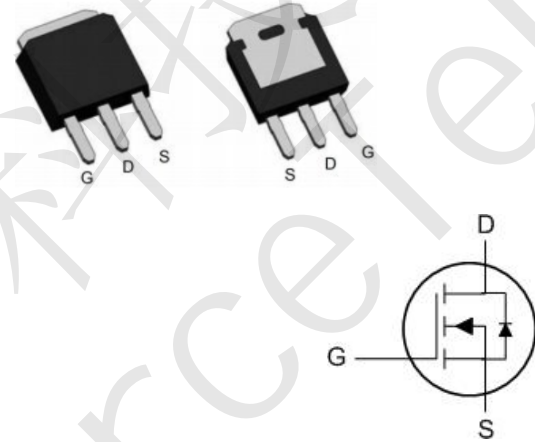
BVDSS	RDSON	ID
100V	88 mΩ	15A

#### CST15N10Z Description

The CST15N10Z is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The CST15N10Z meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

#### CST15N10Z TO251 Pin Configuration



#### CST15N10Z Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	100	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	15	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	8	A
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	3	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	2.4	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	20	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	6.1	mJ
$I_{AS}$	Avalanche Current	10	A
$P_D@T_C=25^\circ C$	Total Power Dissipation <sup>3</sup>	30	W
$P_D@T_A=25^\circ C$	Total Power Dissipation <sup>3</sup>	2	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

#### CST15N10Z Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	6.6	$^\circ C/W$



### CST15N10Z N-Ch 100V Fast Switching MOSFETs

#### CST15N10Z Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	100	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =100V, V <sub>GS</sub> =0V,	-	-	1.0	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1.0	1.5	2.5	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance <small>note3</small>	V <sub>GS</sub> =10V, I <sub>D</sub> =5A	-	88	110	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	96	140	mΩ
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz	-	765	-	pF
C <sub>oss</sub>	Output Capacitance		-	38	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	33	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =50V, I <sub>D</sub> =2A, V <sub>GS</sub> =10V	-	18	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	2.5	-	nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge		-	4	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =50V, I <sub>D</sub> =3A, R <sub>G</sub> =1.8Ω, V <sub>GS</sub> =10V	-	7.5	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	6	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	21	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	9	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	10	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	40	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =10A	-	-	1.2	V
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> =3A, di/dt=100A/μs	-	21	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	22	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

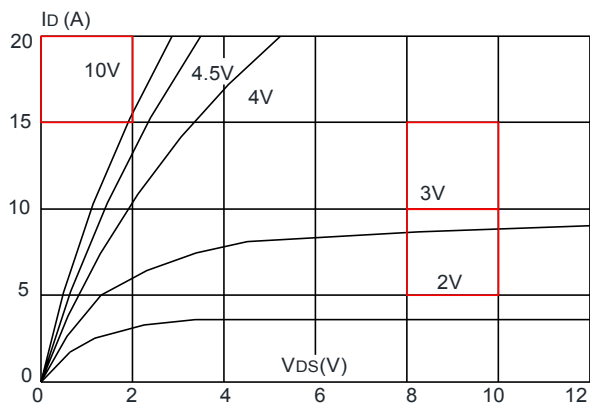
2. EAS condition : T<sub>J</sub>=25°C, V<sub>DD</sub>=30V, V<sub>G</sub>=10V, L=0.5mH, R<sub>G</sub>=25Ω, I<sub>AS</sub>=4A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

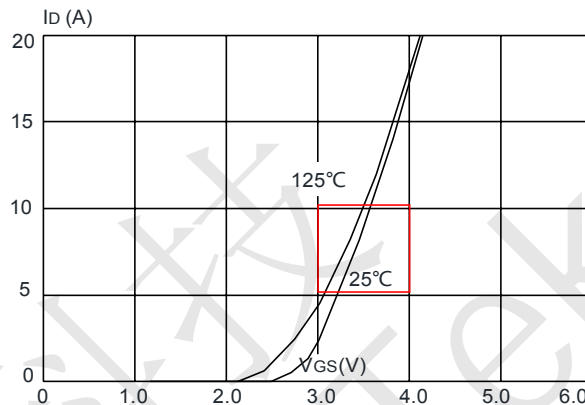


## CST15N10Z Typical Performance Characteristics

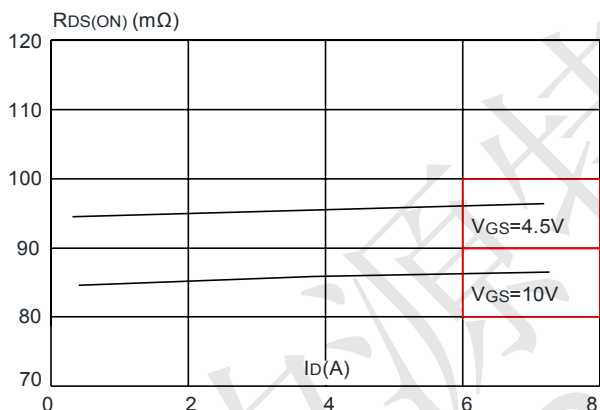
**Figure 1: Output Characteristics**



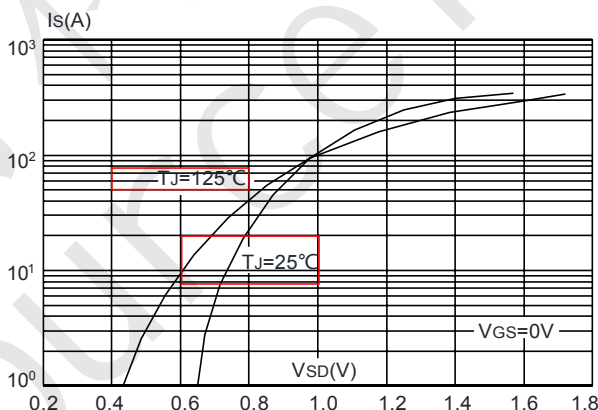
**Figure 2: Typical Transfer Characteristics**



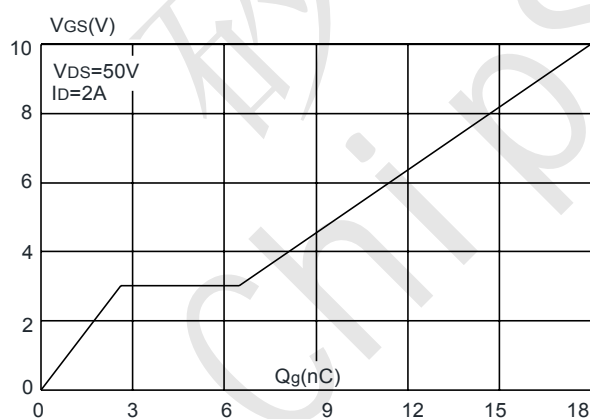
**Figure 3: On-resistance vs. Drain Current**



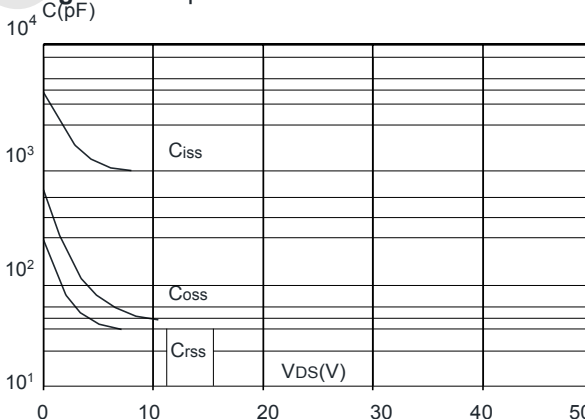
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**



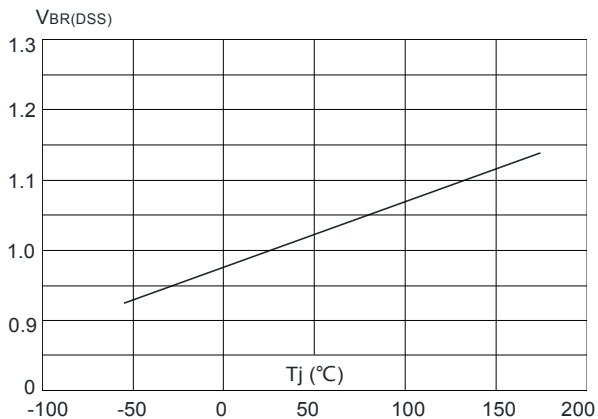
**Figure 6: Capacitance Characteristics**



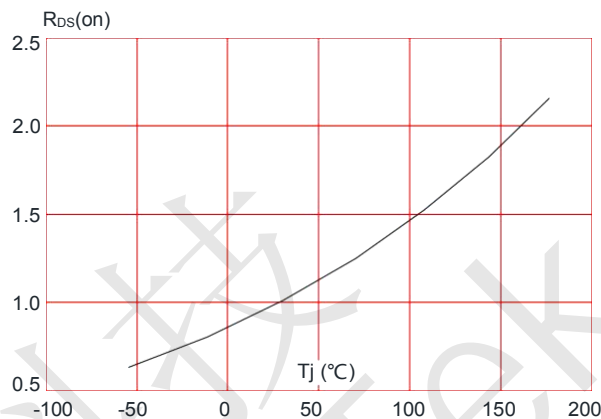


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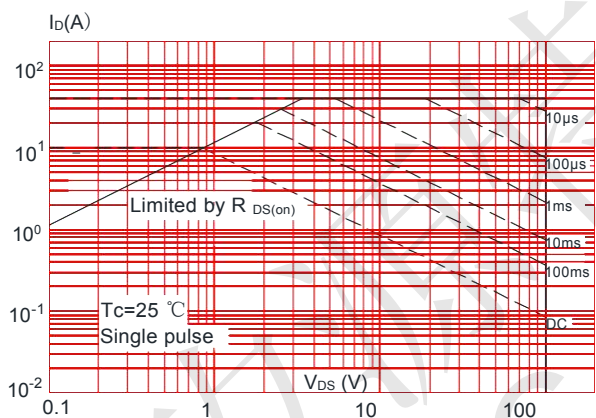
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



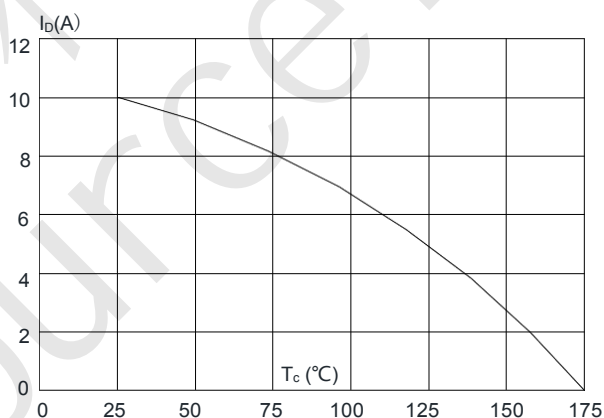
**Figure 8:** Normalized on Resistance vs. Junction Temperature



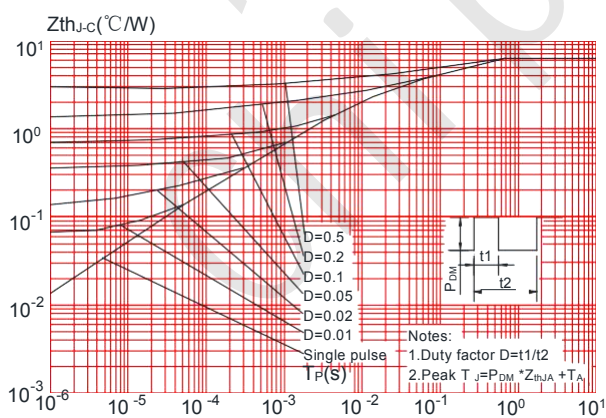
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Case Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case





CST15N10Z Package Mechanical Data TO 251

